# MCAC30P03-TP-VB Datasheet

## P-Channel 30 V (D-S) MOSFET

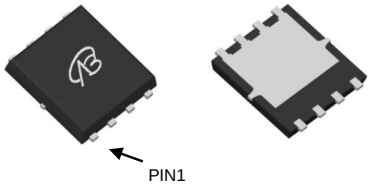
| PRODUCT SUMMARY | | | |
|---|---|---|---|
| $V_{DS}$ (V) | $R_{DS(on)}$ (Ω) | $I_D$ [a] | $Q_g$ (Typ.) |
| - 30 | 0.0080 at $V_{GS}$ = - 10 V | - 60 | 66 nC |
| | 0.0090 at $V_{GS}$ = - 6 V | - 53 | |
| | 0.0120 at $V_{GS}$ = - 4.5 V | - 50 | |

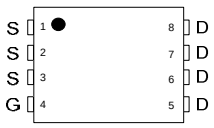
### FEATURES

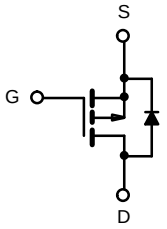
- Extended $V_{GS}$ range (± 25 V) for adaptor switch applications
- Extremely low $R_{DS(on)}$
- Trench Power MOSFET
- 100 % $R_g$ and UIS Tested

Pb-free
RoHS COMPLIANT

DFN5X6




P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25 °C, unless otherwise noted) | | | | |
|---|---|---|---|---|
| Parameter | | Symbol | Limit | Unit |
| Drain-Source Voltage | | $V_{DS}$ | - 30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ± 20 | |
| Continuous Drain Current ($T_J$ = 150 °C) | $T_C$ = 25 °C | $I_D$ | - 60 | A |
| | $T_C$ = 70 °C | | - 50.7 | |
| | $T_A$ = 25 °C | | - 47.3 | |
| | $T_A$ = 70 °C | | - 43.9 [b, c] | |
| Pulsed Drain Current (t = 300 µs) | | $I_{DM}$ | - 150 | |
| Continuous Source-Drain Diode Current | $T_C$ = 25 °C | $I_S$ | - 58 [b, c] | |
| | $T_A$ = 25 °C | | - 46 [b, c] | |
| Single Pulse Avalanche Current | L = 0.1 mH | $I_{AS}$ | - 40 | |
| Single Pulse Avalanche Energy | | $E_{AS}$ | 80 | mJ |
| Maximum Power Dissipation | $T_C$ = 25 °C | $P_D$ | 75 | W |
| | $T_C$ = 70 °C | | 40 | |
| | $T_A$ = 25 °C | | 3.1 [b, c] | |
| | $T_A$ = 70 °C | | 2 [b, c] | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|---|---|---|---|---|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient [b, d] | t ≤ 10 s | $R_{thJA}$ | 33 | 40 | °C/W |
| Maximum Junction-to-Foot (Drain) | Steady State | $R_{thJF}$ | 15 | 17 | |

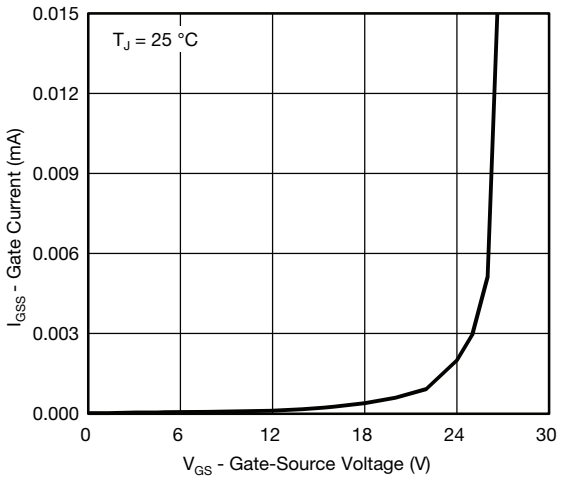
Notes:
a. Based on $T_C$ = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 90 °C/W.

| **SPECIFICATIONS** ($T_J$ = 25 °C, unless otherwise noted) | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | **Min.** | **Typ.** | **Max.** | **Unit** |
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = - 250 µA | - 30 | | | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D$ = - 250 µA | | - 24 | | mV/°C |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | 6 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$ , $I_D$ = - 250 µA | - 1.0 | | - 2.5 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 25 V | | | ± 150 | µA |
| | | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | | | ± 15 | |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = - 30 V, $V_{GS}$ = 0 V | | | - 1 | |
| | | $V_{DS}$ = - 30 V, $V_{GS}$ = 0 V, $T_J$ = 55 °C | | | - 10 | |
| On-State Drain Current[a] | $I_{D(on)}$ | $V_{DS} \leq$ - 5 V, $V_{GS}$ = - 10 V | - 20 | | | A |
| Drain-Source On-State Resistance[a] | $R_{DS(on)}$ | $V_{GS}$ = - 10 V, $I_D$ = - 13 A | | 0.0080 | | Ω |
| | | $V_{GS}$ = - 6 V, $I_D$ = - 10 A | | 0.0090 | | |
| | | $V_{GS}$ = - 4.5 V, $I_D$ = - 8 A | | 0.0120 | | |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = - 15 V, $I_D$ = - 13 A | | 44 | | S |
| **Dynamic[b]** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ = - 15 V, $V_{GS}$ = 0 V, f = 1 MHz | | 4620 | | pF |
| Output Capacitance | $C_{oss}$ | | | 880 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 820 | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = - 15 V, $V_{GS}$ = - 10 V, $I_D$ = - 17.3 A | | 102 | 153 | nC |
| | | $V_{DS}$ = - 15 V, $V_{GS}$ = - 5 V, $I_D$ = - 17.3 A | | 66 | 80 | |
| Gate-Source Charge | $Q_{gs}$ | | | 16 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 28 | | |
| Gate Resistance | $R_g$ | f = 1 MHz | 0.3 | 1.3 | 2.6 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 0 V, $R_L$ = 1.5 Ω<br>$I_D \cong$ - 10 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 Ω | | 70 | 105 | ns |
| Rise Time | $t_r$ | | | 70 | 105 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 45 | 68 | |
| Fall Time | $t_f$ | | | 27 | 41 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = - 15 V, $R_L$ = 1.5 Ω<br>$I_D \cong$ - 10 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 Ω | | 18 | 30 | |
| Rise Time | $t_r$ | | | 15 | 25 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 52 | 80 | |
| Fall Time | $t_f$ | | | 14 | 25 | |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | $T_C$ = 25 °C | | | - 5.8 | A |
| Pulse Diode Forward Current | $I_{SM}$ | | | | - 60 | |
| Body Diode Voltage | $V_{SD}$ | $I_S$ = - 10 A, $V_{GS}$ = 0 V | | - 0.78 | - 1.2 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $I_F$ = - 10 A, dI/dt = 100 A/µs, $T_J$ = 25 °C | | 35 | 53 | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | | 25 | 38 | nC |
| Reverse Recovery Fall Time | $t_a$ | | | 19 | | ns |
| Reverse Recovery Rise Time | $t_b$ | | | 16 | | |

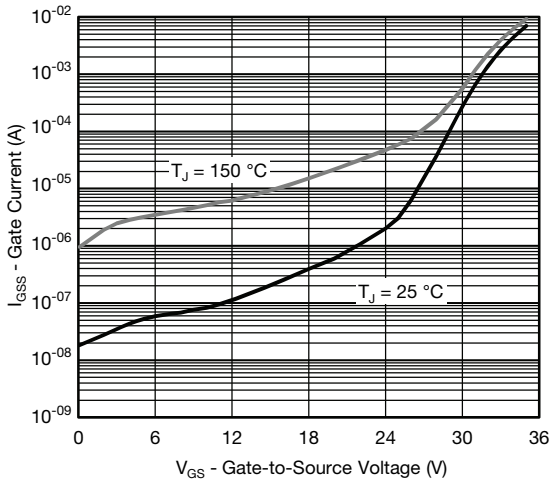
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

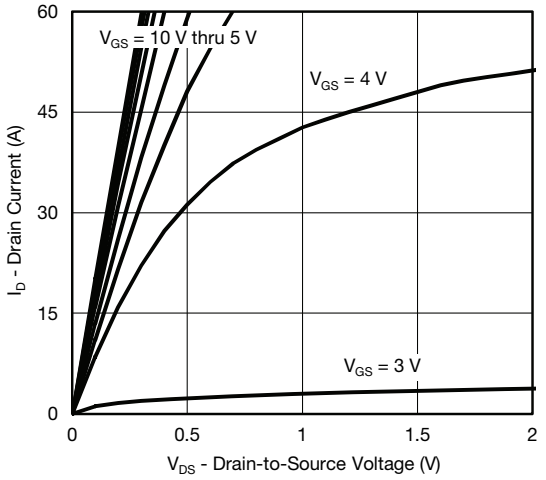
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



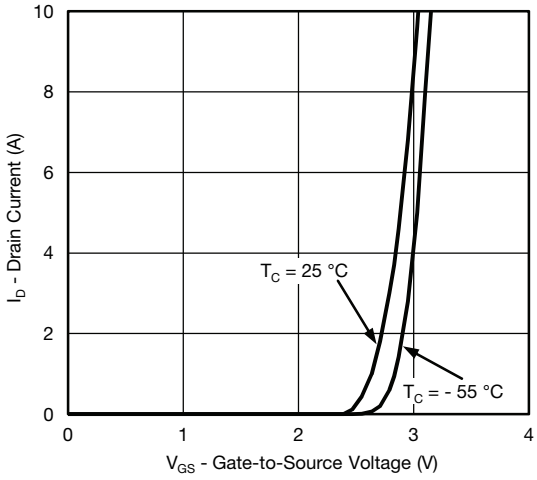

**Gate Current vs. Gate-Source Voltage**



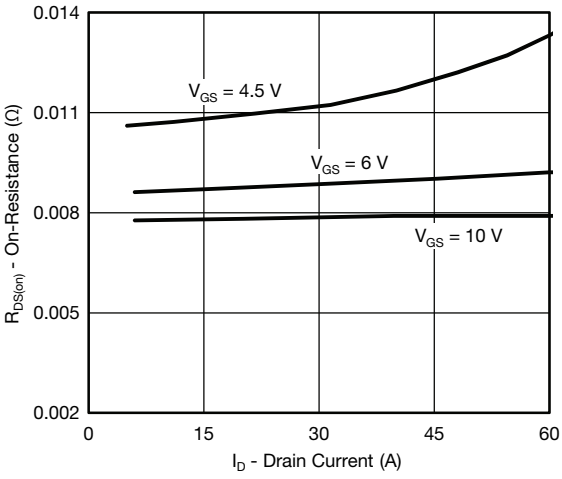

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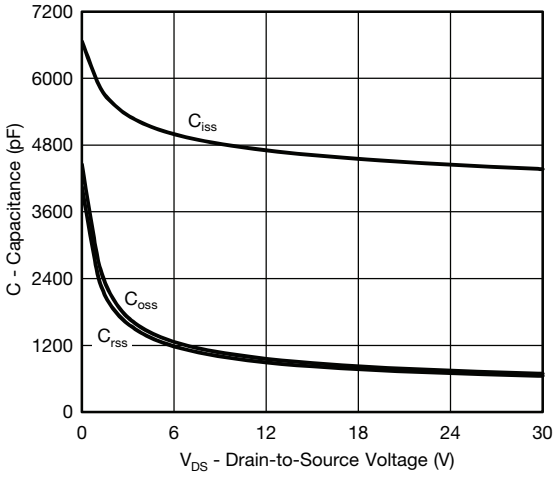

**Output Characteristics**




**Transfer Characteristics**

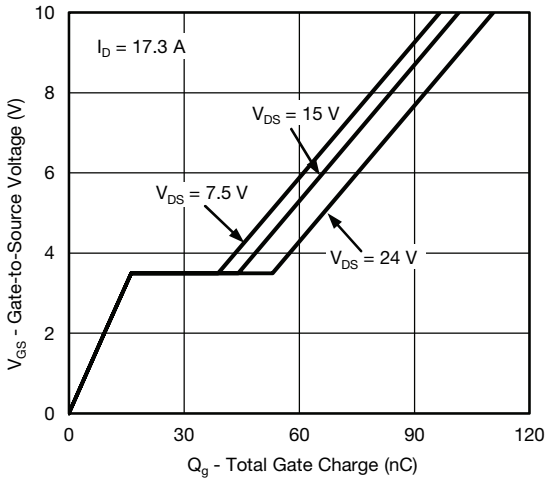



**On-Resistance vs. Drain Current**

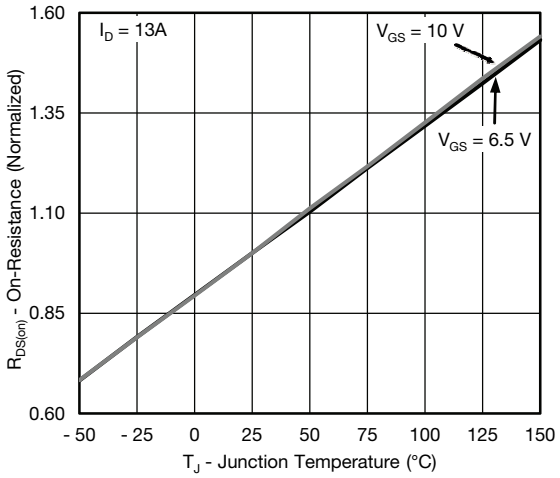



**Capacitance**

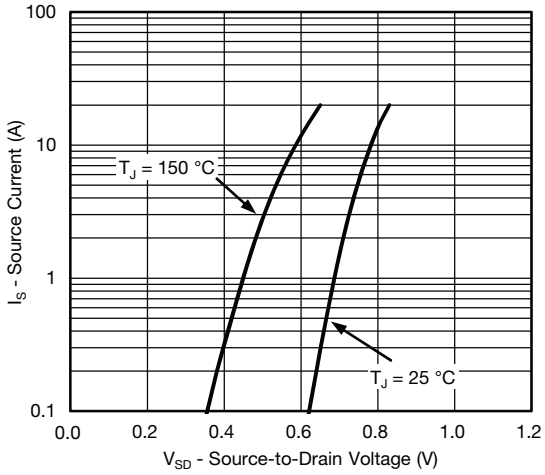
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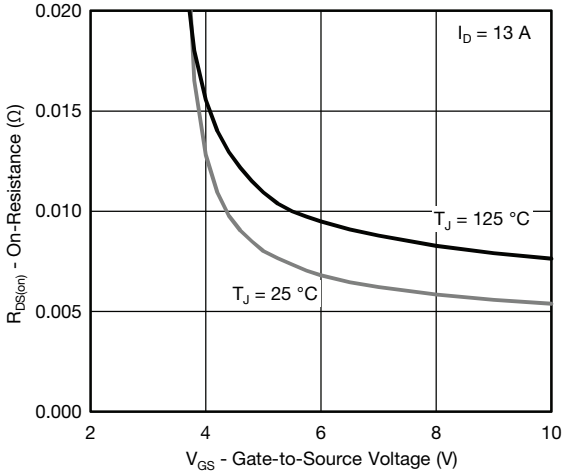

**Gate Charge**



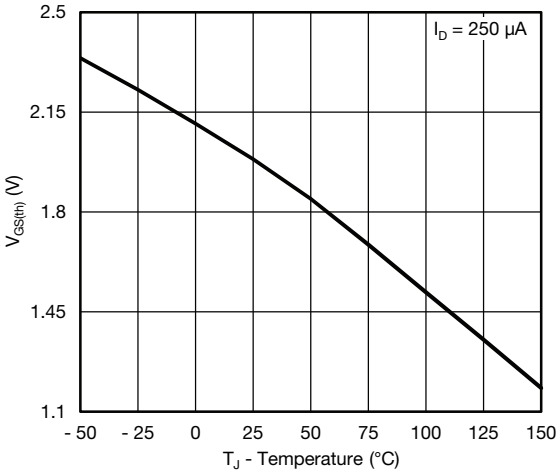

**On-Resistance vs. Junction Temperature**



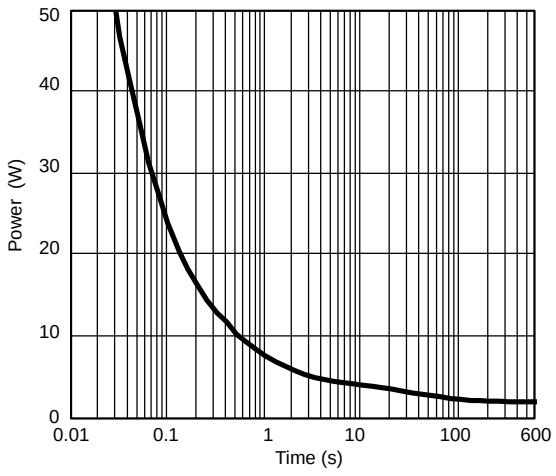

**Source-Drain Diode Forward Voltage**




**On-Resistance vs. Gate-to-Source Voltage**

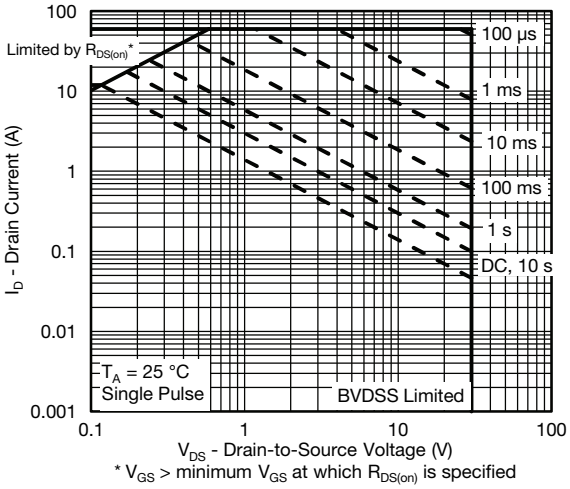



**Threshold Voltage**

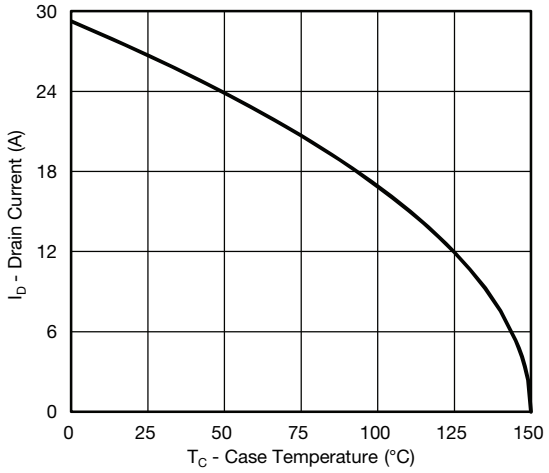



**Single Pulse Power, Junction-to-Ambient**

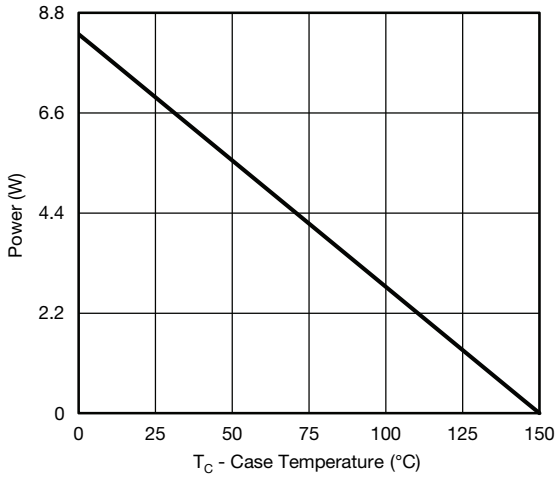
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



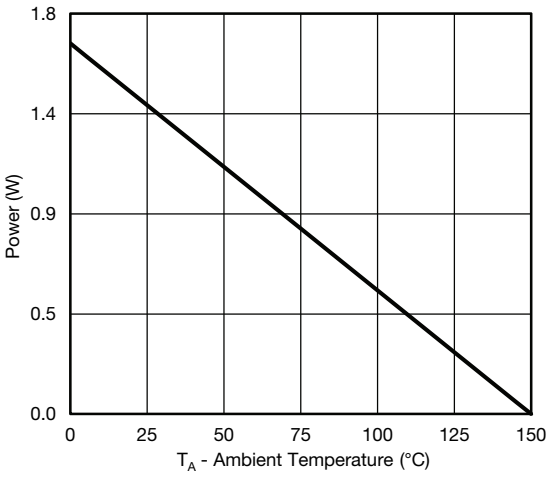

**Safe Operating Area, Junction-to-Ambient**




**Current Derating***



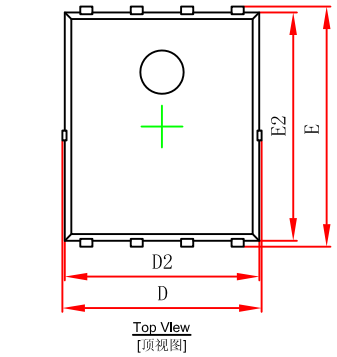

**Power Junction-to-Foot**

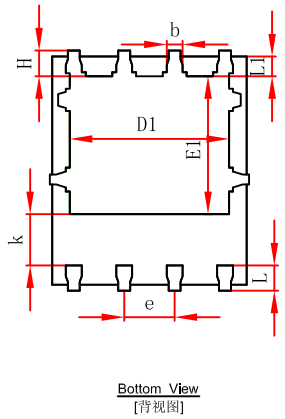


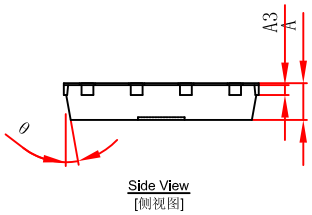

**Power Junction-to-Ambient**

* The power dissipation $P_D$ is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## PDFNWB5x6-8L Package Outline Dimensions

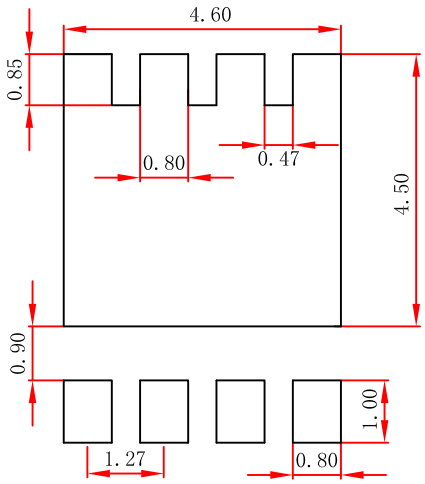



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|---|---|---|---|---|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.000 | 0.035 | 0.039 |
| A3 | 0.254REF. | | 0.010REF. | |
| D | 4.944 | 5.096 | 0.195 | 0.201 |
| E | 5.974 | 6.126 | 0.235 | 0.241 |
| D1 | 3.910 | 4.110 | 0.154 | 0.162 |
| E1 | 3.375 | 3.575 | 0.133 | 0.141 |
| D2 | 4.824 | 4.976 | 0.190 | 0.196 |
| E2 | 5.674 | 5.826 | 0.223 | 0.229 |
| k | 1.190 | 1.390 | 0.047 | 0.055 |
| b | 0.350 | 0.450 | 0.014 | 0.018 |
| e | 1.270TYP. | | 0.050TYP. | |
| L | 0. | 0. | 0. | 0. |
| L1 | 5590. | 7110. | 0220. | 0280. |
| H | 4240. | 5760. | 0170. | 0230. |
| θ | 574<br>10° | 726<br>12° | 023<br>10° | 029<br>12° |

## PDFNWB5x6-8L Suggested Pad Layout




Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

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